



Shantou Huashan Electronic Devices Co., Ltd.

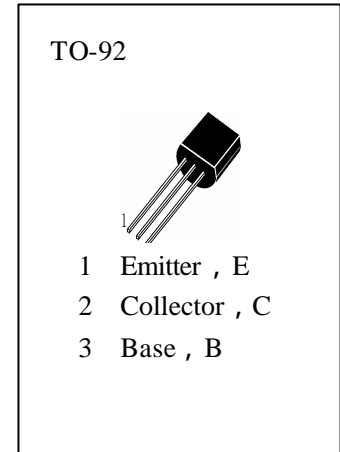
NPN SILICON TRANSISTOR

HD965

LOW FREQUENCY AMPLIFIER APPLICATIONS.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	—Storage Temperature.....	-55~150
T_j	—Junction Temperature.....	150
P_C	—Collector Dissipation.....	0.75W
V_{CBO}	—Collector-Base Voltage.....	40V
V_{CEO}	—Collector-Emitter Voltage.....	20V
V_{EBO}	—Emitter-Base Voltage.....	7V
I_C	—Collector Current.....	5A



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCEO	Collector-Emitter Breakdown Voltage	20			V	$I_C=1mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	7			V	$I_E=10\mu A, I_C=0$
ICBO	Collector Cut-off Current			100	nA	$V_{CB}=10V, I_E=0$
IEBO	Emitter Cut-off Current			100	nA	$V_{EB}=7V, I_C=0$
HFE (1)	DC Current Gain	180		800		$V_{CE}=2V, I_C=0.5A$
HFE (2)	DC Current Gain	150				$V_{CE}=2V, I_C=2A$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			1	V	$I_C=3A, I_B=0.1A$
f_T	Current Gain-Bandwidth Product	150			MHz	$V_{CE}=6V, I_C=50mA$
Cob	Output Capacitance			50	pF	$V_{CB}=20V, I_E=0, f=1MHz$